

iscN-Channel MOSFET Transistor

IRFS11N50A

• FEATURES

- Low drain-source on-resistance: R_{DS}(ON) =0.52Ω (MAX)
- Enhancement mode: Vth = 2.0 to 4.0V (VDS = 10 V, ID=0.25mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

· Switching Voltage Regulators

PAK 2 G(1) S(3) pin 1.Gate 2.Drain 3.Source TO-263 package

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	500	V
V _G s	Gate-Source Voltage	±30	V
l _D	Drain Current-Continuous	11	Α
Ірм	Drain Current-Single Pulsed	44	А
P_D	Total Dissipation @Tc=25°C	170	W
Tj	Max. Operating Junction Temperature	-55~150	${\mathbb C}$
T _{stg}	Storage Temperature	-55~150	${\mathbb C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	0.75	°C/W	

J	A B D	K	Q 7	Ls
F	⊢∔G		m	v #
- 1	DIM	MIN	MAX 0	
	A		6.8	
- 1	В	6.6		-
-	C	15.23	15.25	-
	D	10.15	10.17	1
- 3	F G	0.76	0.78	-
1	Н	1.26 1.4	1.28 1.6	1
8	J	1.33	1.35	1
	K	0.4	0.6	
	L	4.6	4.8	
-	ō	8 60	8.71	1
9	R	8.69 5.28	5.30	1
3	S	1.26	1.28	1
	Ü	0.0	0.2	1
				The second second
	v	0.37	0.39	1



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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 0.25mA	500			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = 10V; I _D =0.25mA	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =6.6A			0.52	Ω
lgss	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} = 0V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =500V; V _{GS} = 0V V _{DS} =400V; V _{GS} = 0V;T _J =125°C			25 250	uA
V _{SDF}	Diode forward voltage	I _{DR} =11A, V _{GS} = 0 V			1.5	V

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